



# 80RIA SERIES

## PHASE CONTROL THYRISTORS

**Stud Version**

80A

### Features

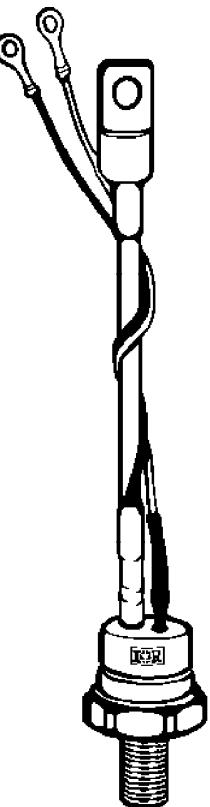
- All diffused design
- Glass-metal seal up to 1200V
- International standard case TO-209AC (TO-94)
- Threaded studs UNF 1/2 - 20UNF2A or ISO M12x1.75

### Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

### Major Ratings and Characteristics

Parameters	80RIA	Unit
$I_{T(AV)}$	80	A
@ $T_c$	85	°C
$I_{T(RMS)}$	125	A
$I_{TSM}$	1900	A
@ 50Hz	1990	A
$I^2t$	18	KA <sup>2</sup> s
@ 60Hz	16	KA <sup>2</sup> s
$V_{DRM}/V_{RRM}$	400 to 1200	V
$t_q$ typical	110	μs
$T_J$	- 40 to 125	°C



case style  
TO-209AC (TO-94)

# 80RIA Series

## ELECTRICAL SPECIFICATIONS

### Voltage Ratings

Type number	Voltage Code	$V_{DRM}/V_{RRM}$ , max. repetitive peak and off-state voltage V	$V_{RSM}$ , maximum non-repetitive peak voltage V	$I_{DRM}/I_{RRM}$ max. @ $T_J = 125^\circ C$ mA
80RIA	40	400	500	15
	80	800	900	
	120	1200	1300	

### On-state Conduction

Parameter	80RIA	Units	Conditions				
$I_{T(AV)}$	Max. average on-state current @ Case temperature	A	180° conduction, half sine wave				
		°C					
$I_{T(RMS)}$	Max. RMS on-state current	A	DC @ 75°C case temperature				
$I_{TSM}$	Max. peak, one-cycle non-repetitive surge current	1900	A	t = 10ms	No voltage reapplied	Sinusoidal half wave, Initial $T_J = T_J$ max.	
		1990		t = 8.3ms			
		1600		t = 10ms	100% $V_{RRM}$ reapplied		
		1675		t = 8.3ms			
$I^2t$	Maximum $I^2t$ for fusing	18	KA <sup>2</sup> s	t = 10ms	No voltage reapplied	Initial $T_J = T_J$ max.	
		16		t = 8.3ms			
		12.7		t = 10ms	100% $V_{RRM}$ reapplied		
		11.7		t = 8.3ms			
$I^2\sqrt{t}$	Maximum $I^2\sqrt{t}$ for fusing	180.5	KA <sup>2</sup> \sqrt{s}	t = 0.1 to 10ms, no voltage reapplied			
$V_{T(TO)1}$	Low level value of threshold voltage	0.99	V	(16.7% $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ ), $T_J = T_J$ max.			
$V_{T(TO)2}$	High level value of threshold voltage	1.13		$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ max.			
$r_{t1}$	Low level value of on-state slope resistance	2.29	mΩ	(16.7% $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ ), $T_J = T_J$ max.			
$r_{t2}$	High level value of on-state slope resistance	1.84		$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ max.			
$V_{TM}$	Max. on-state voltage	1.60	V	$I_{pk} = 250A$ , $T_J = 25^\circ C$ $t_p = 10ms$ sine pulse			
$I_H$	Maximum holding current	150	mA	$T_J = 25^\circ C$ , anode supply 12V resistive load			
$I_L$	Typical latching current	400					

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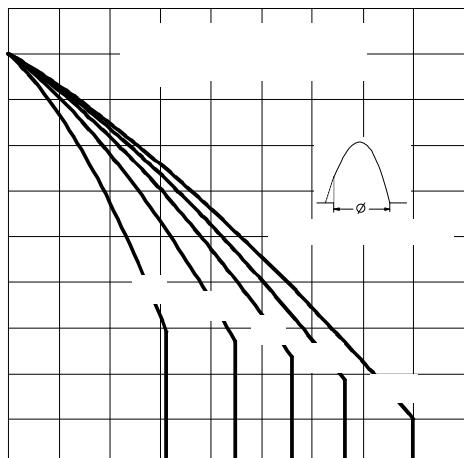


Fig. 1 - Current Ratings Characteristics

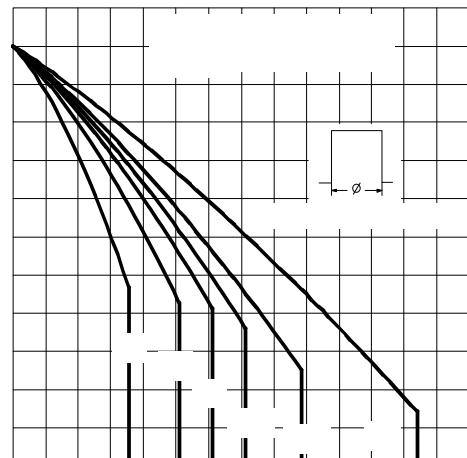


Fig. 2 - Current Ratings Characteristics

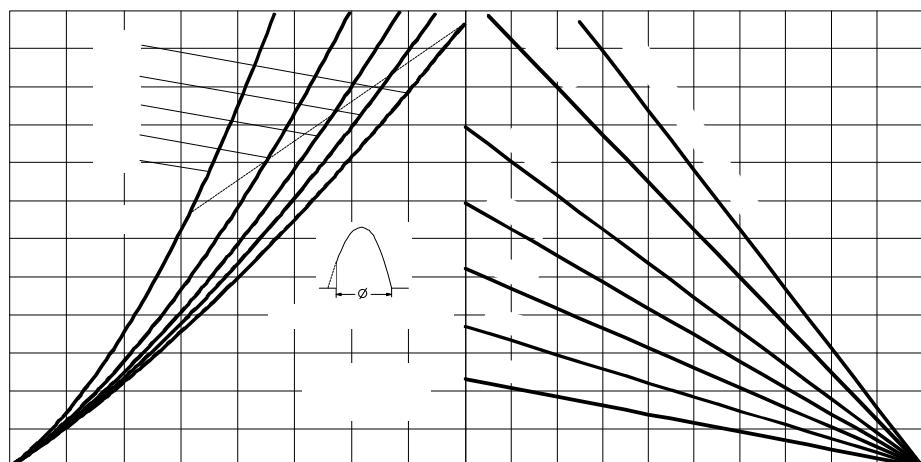


Fig. 3 - On-state Power Loss Characteristics

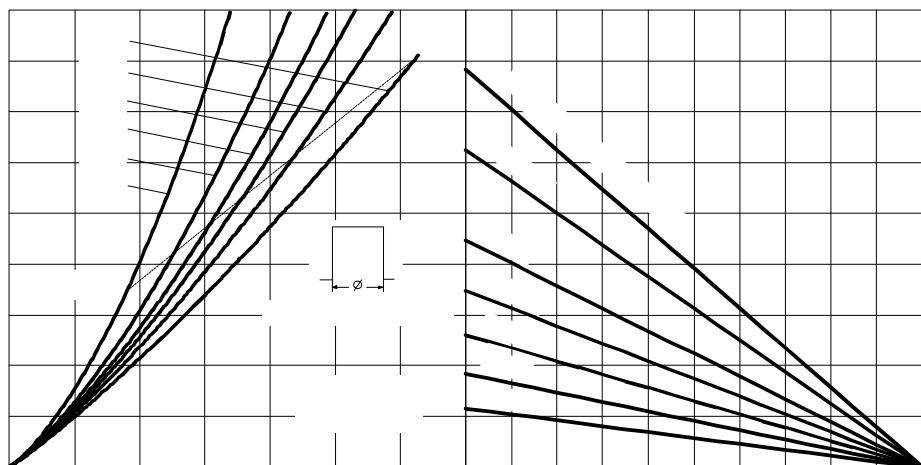


Fig. 4 - On-state Power Loss Characteristics

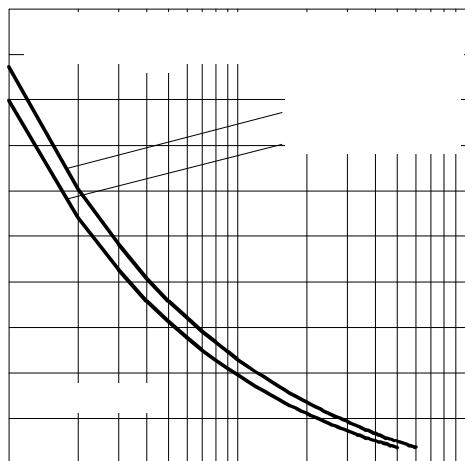


Fig. 5 - Maximum Non-Repetitive Surge Current

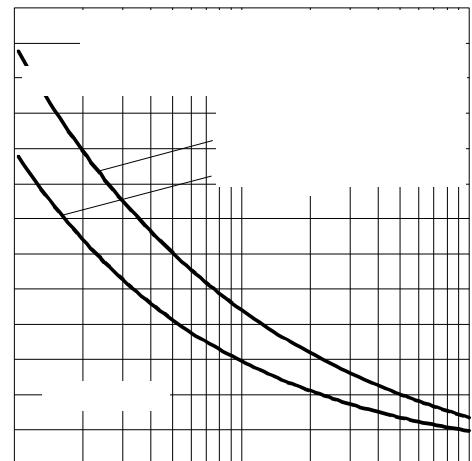


Fig. 6 - Maximum Non-Repetitive Surge Current

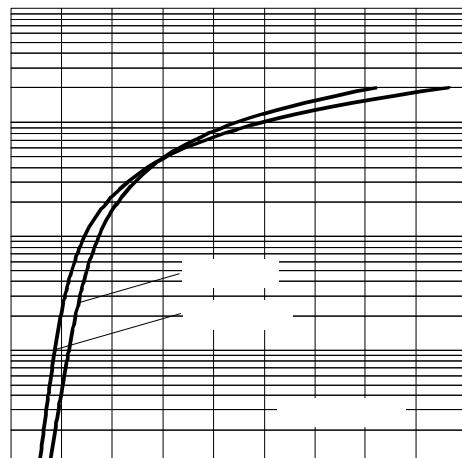


Fig. 7 - On-state Voltage Drop Characteristics

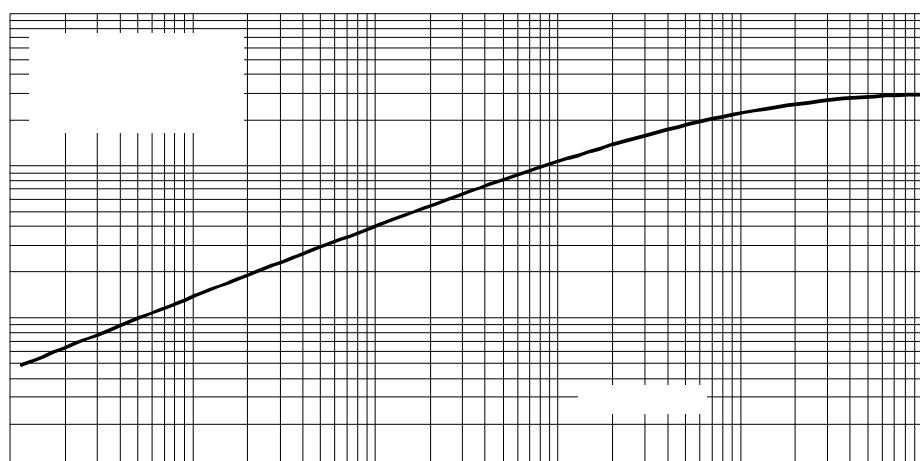


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

## 80RIA Series

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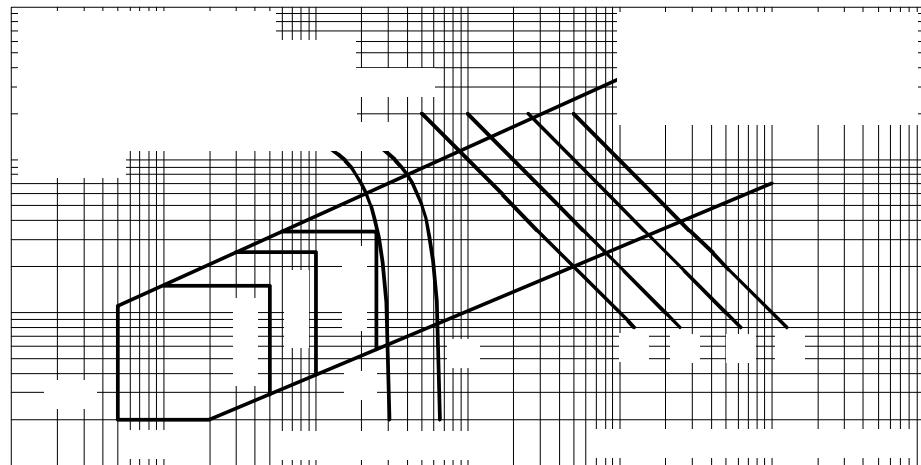


Fig. 9 - Gate Characteristics

## Switching

Parameter	80RIA	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	300	A/μs	$T_J = 125^\circ\text{C}$ , $V_d = \text{rated } V_{\text{DRM}}$ , $I_{\text{TM}} = 2x\text{di/dt snubber } 0.2\mu\text{F}, 15\Omega$ , Gate pulse: 20V, 65Ω, $t_p = 6\mu\text{s}$ , $t_r = 0.5\mu\text{s}$ Per JEDEC Standard RS-397, 5.2.2.6.
$t_d$ Typical delay time	1	μs	Gate pulse: 10V, 15Ω source, $t_p = 6\mu\text{s}$ , $t_r = 0.1\mu\text{s}$ , $V_d = \text{rated } V_{\text{DRM}}$ , $I_{\text{TM}} = 50\text{A}$ , $T_J = 25^\circ\text{C}$ .
$t_q$ Typical turn-off time	110		$I_{\text{TM}} = 50\text{A}$ , $T_J = T_J \text{ max}$ , $\text{di/dt} = -5\text{A}/\mu\text{s min.}$ , $V_R = 50\text{V}$ , $\text{dv/dt} = 20\text{V}/\mu\text{s}$ , Gate bias: 0V 25Ω, $t_p = 500\mu\text{s}$

## Blocking

Parameter	80RIA	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/μs	$T_J = 125^\circ\text{C}$ exponential to 67% rated $V_{\text{DRM}}$
$I_{\text{RRM}}$ Max. peak reverse and off-state leakage current	15	mA	$T_J = 125^\circ\text{C}$ rated $V_{\text{DRM}}/V_{\text{RRM}}$ applied

## Triggering

Parameter	80RIA	Units	Conditions
$P_{\text{GM}}$ Maximum peak gate power	12	W	$T_J = T_J \text{ max}$ , $t_p \leq 5\text{ms}$
$P_{\text{G(AV)}}$ Maximum average gate power	3		$T_J = T_J \text{ max}$ , $f = 50\text{Hz}$ , $d\% = 50$
$I_{\text{GM}}$ Max. peak positive gate current	3	A	$T_J = T_J \text{ max}$ , $t_p \leq 5\text{ms}$
$+V_{\text{GM}}$ Maximum peak positive gate voltage	20	V	
$-V_{\text{GM}}$ Maximum peak negative gate voltage	10		$T_J = T_J \text{ max}$ , $t_p \leq 5\text{ms}$
$I_{\text{GT}}$ Max. DC gate current required to trigger	270 120 60	mA	$T_J = -40^\circ\text{C}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$ Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 6V anode-to-cathode applied
$V_{\text{GT}}$ Max. DC gate voltage required to trigger	3.5 2.5 1.5	V	$T_J = -40^\circ\text{C}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
$I_{\text{GD}}$ DC gate current not to trigger	6	mA	$T_J = T_J \text{ max}$ Max. gate current/ voltage not to trigger is the max. value which will not trigger any unit with rated $V_{\text{DRM}}$ anode-to-cathode applied
$V_{\text{GD}}$ DC gate voltage not to trigger	0.25	V	

## 80RIA Series

### Thermal and Mechanical Specification

Parameter	80RIA	Units	Conditions
$T_J$	Max. operating temperature range	-40 to 125	$^{\circ}\text{C}$
$T_{\text{stg}}$	Max. storage temperature range	-40 to 150	
$R_{\text{thJC}}$	Max. thermal resistance, junction to case	0.30	K/W
$R_{\text{thCS}}$	Max. thermal resistance, case to heatsink	0.1	
T	Mounting torque, $\pm 10\%$	15.5 (137)	Nm (lbf-in)
		14 (120)	
wt	Approximate weight	130	g
Case style	TO-209AC(TO-94)	See Outline Table	

### $\Delta R_{\text{thJ-C}}$ Conduction

(The following table shows the increment of thermal resistance  $R_{\text{thJ-C}}$  when devices operate at different conduction angles than DC)

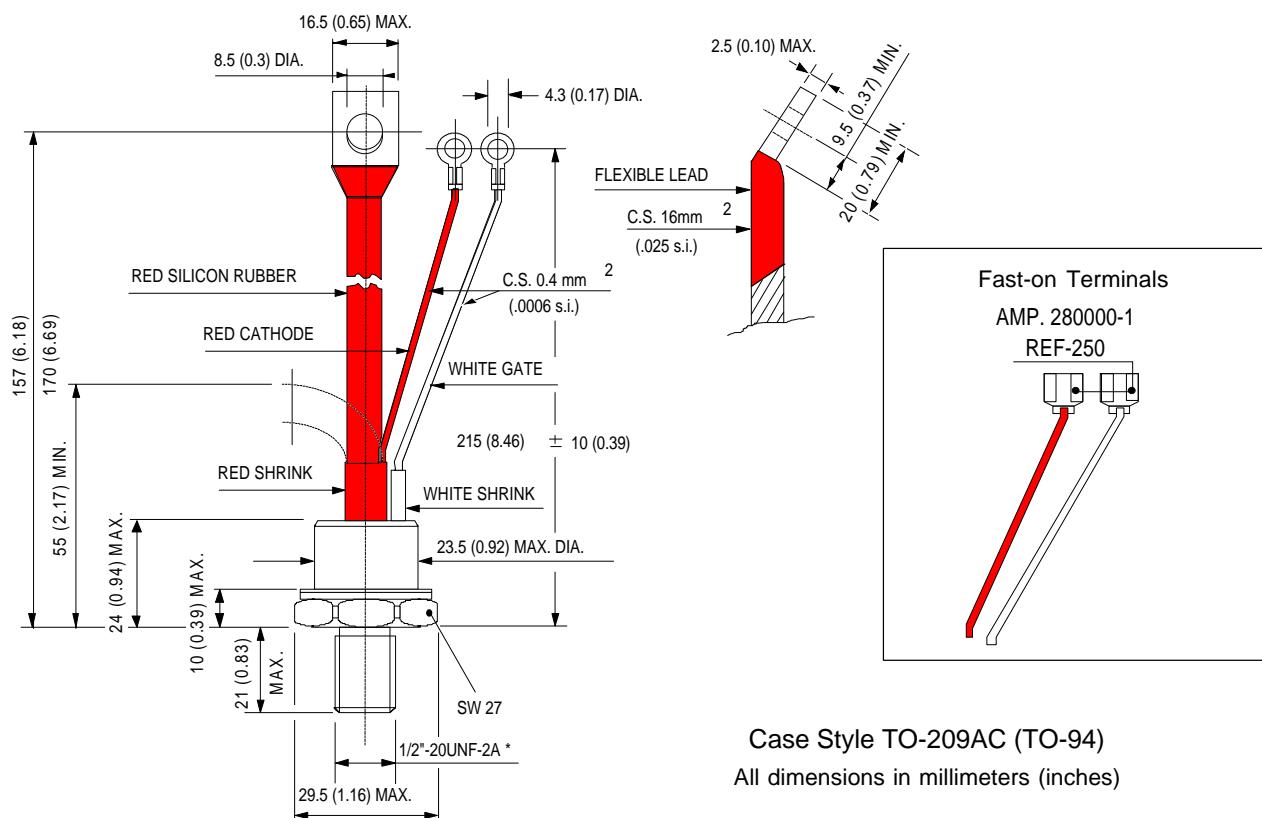
Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.042	0.030	K/W	$T_J = T_{\text{J max.}}$
120°	0.050	0.052		
90°	0.064	0.070		
60°	0.095	0.100		
30°	0.164	0.165		

### Ordering Information Table

Device Code	8	0	RIA	120	M
1	1	2	3	4	5
2	-	I <sub>TAV</sub> x 10A			
3	-	0 = Eyelet terminals (Gate and Auxiliary Cathode Leads)			
		1 = Fast - on terminals (Gate and Auxiliary Cathode Leads)			
		2 = Flag terminals (For Cathode and Gate Terminals)			
4	-				
5	-				
		RIA = Essential part number			
		4 - Voltage code: Code x 10 = V <sub>RRM</sub> (See Voltage Rating Table)			
		5 - None = Stud base 1/2 "20UNF - 2A threads			
		M = Stud base metric threads M12 x 1.75 E 6			

## Outline Table

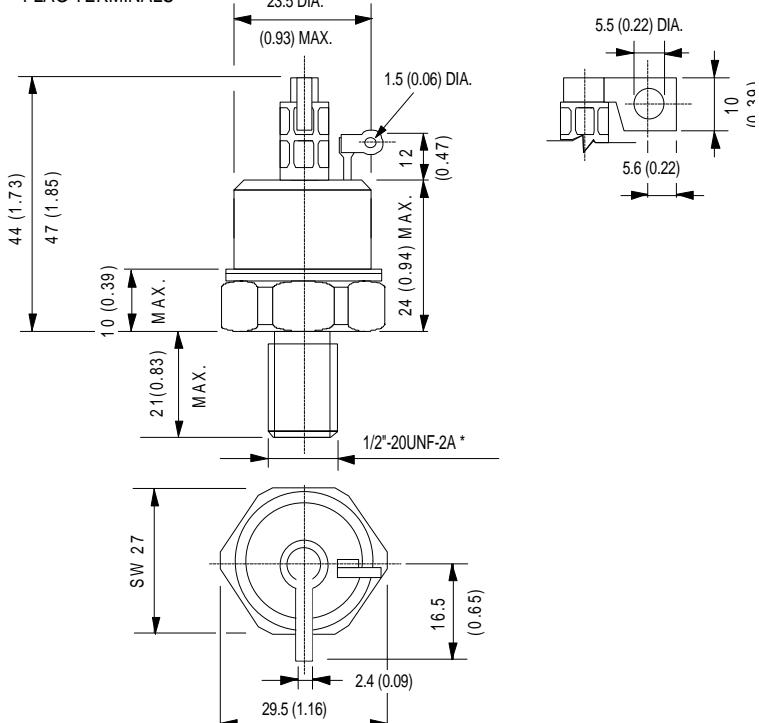
## GLASS METAL SEAL



\* FOR METRIC DEVICE : M12 x 1.75 E 6

## GLASS-METAL SEAL

## FLAG TERMINALS



\* FOR METRIC DEVICE: M12 x 1.75 E 6